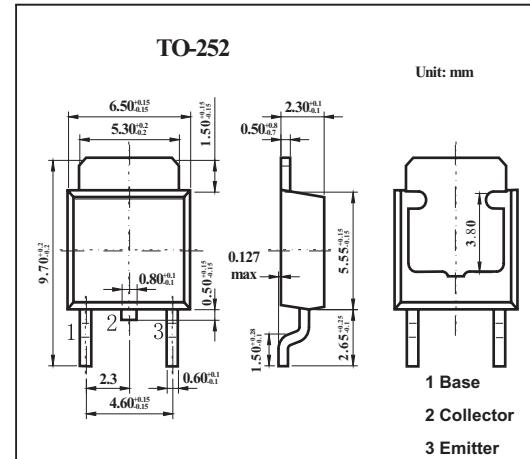


Silicon PNP Epitaxial Planar Type**2SB967****■ Features**

- Possible to solder the radiation fin directly to printed circuit board.
- Low collector-emitter saturation voltage V_{CE(sat)}.
- Large collector current I_C.

■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-27	V
Collector-emitter voltage	V _{CEO}	-18	V
Emitter-base voltage	V _{EBO}	-7	V
Collector current	I _C	-5	A
Peak collector current	I _{CP}	-8	A
Collector power dissipation	P _C	20	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base cutoff current	I _{CBO}	V _{CB} = -10 V, I _E = 0			-100	nA
Emitter-base cutoff current	I _{EBO}	V _{EB} = -5 V, I _C = 0			-1	μA
Collector-emitter voltage	V _{CEO}	I _C = -1mA, I _B = 0	-18			V
Emitter-base voltage	V _{EBO}	I _E = -10 μA, I _C = 0	-7			V
Forward current transfer ratio	h _{FE}	V _{CE} = -2 V, I _C = 2 A	90		625	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -3 A, I _B = -0.1 A			-1	V
Transition frequency	f _T	V _{CE} = -6 V, I _E = -50 mA, f = 200 MHz	120			MHz
Collector output capacitance	C _{ob}	V _{CB} = -20V, I _E = 0, f = 1.0MHz			85	pF

■ hFE Classification

Rank	P	Q	R
h _{FE}	90~135	125~205	180~625